Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	8051
Core Size	8-Bit
Speed	67MHz
Connectivity	EBI/EMI, I²C, LINbus, SPI, UART/USART
Peripherals	CapSense, DMA, POR, PWM, WDT
Number of I/O	62
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 16x12b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c3665axi-198t

Table 4-1. Arithmetic Instructions

Mnemonic	Description	Bytes	Cycles
ADD A,Rn	Add register to accumulator	1	1
ADD A,Direct	Add direct byte to accumulator	2	2
ADD A,@Ri	Add indirect RAM to accumulator	1	2
ADD A,#data	Add immediate data to accumulator	2	2
ADDC A,Rn	Add register to accumulator with carry	1	1
ADDC A,Direct	Add direct byte to accumulator with carry	2	2
ADDC A,@Ri	Add indirect RAM to accumulator with carry	1	2
ADDC A,#data	Add immediate data to accumulator with carry	2	2
SUBB A,Rn	Subtract register from accumulator with borrow	1	1
SUBB A,Direct	Subtract direct byte from accumulator with borrow	2	2
SUBB A,@Ri	Subtract indirect RAM from accumulator with borrow	1	2
SUBB A,#data	Subtract immediate data from accumulator with borrow	2	2
INC A	Increment accumulator	1	1
INC Rn	Increment register	1	2
INC Direct	Increment direct byte	2	3
INC @Ri	Increment indirect RAM	1	3
DEC A	Decrement accumulator	1	1
DEC Rn	Decrement register	1	2
DEC Direct	Decrement direct byte	2	3
DEC @Ri	Decrement indirect RAM	1	3
INC DPTR	Increment data pointer	1	1
MUL	Multiply accumulator and B	1	2
DIV	Divide accumulator by B	1	6
DAA	Decimal adjust accumulator	1	3

4.3.1.2 Logical Instructions

The logical instructions perform Boolean operations such as AND, OR, XOR on bytes, rotate of accumulator contents, and swap of nibbles in an accumulator. The Boolean operations on the bytes are performed on the bit-by-bit basis. Table 4-2 on page 15 shows the list of logical instructions and their description.

Table 4-2. Logical Instructions

Mnemonic	Description	Bytes	Cycles
ANL A,Rn	AND register to accumulator	1	1
ANL A,Direct	AND direct byte to accumulator	2	2
ANL A,@Ri	AND indirect RAM to accumulator	1	2
ANL A,#data	AND immediate data to accumulator	2	2
ANL Direct, A	AND accumulator to direct byte	2	3
ANL Direct, #data	AND immediate data to direct byte	3	3
ORL A,Rn	OR register to accumulator	1	1
ORL A,Direct	OR direct byte to accumulator	2	2
ORL A,@Ri	OR indirect RAM to accumulator	1	2

Table 4-3. Data Transfer Instructions *(continued)*

Mnemonic	Description	Bytes	Cycles
MOV @Ri, Direct	Move direct byte to indirect RAM	2	3
MOV @Ri, #data	Move immediate data to indirect RAM	2	2
MOV DPTR, #data16	Load data pointer with 16 bit constant	3	3
MOVC A, @A+DPTR	Move code byte relative to DPTR to accumulator	1	5
MOVC A, @A + PC	Move code byte relative to PC to accumulator	1	4
MOVX A,@Ri	Move external RAM (8-bit) to accumulator	1	4
MOVX A, @DPTR	Move external RAM (16-bit) to accumulator	1	3
MOVX @Ri, A	Move accumulator to external RAM (8-bit)	1	5
MOVX @DPTR, A	Move accumulator to external RAM (16-bit)	1	4
PUSH Direct	Push direct byte onto stack	2	3
POP Direct	Pop direct byte from stack	2	2
XCH A, Rn	Exchange register with accumulator	1	2
XCH A, Direct	Exchange direct byte with accumulator	2	3
XCH A, @Ri	Exchange indirect RAM with accumulator	1	3
XCHD A, @Ri	Exchange low order indirect digit RAM with accumulator	1	3

Table 4-4. Boolean Instructions

Mnemonic	Description	Bytes	Cycles
CLR C	Clear carry	1	1
CLR bit	Clear direct bit	2	3
SETB C	Set carry	1	1
SETB bit	Set direct bit	2	3
CPL C	Complement carry	1	1
CPL bit	Complement direct bit	2	3
ANL C, bit	AND direct bit to carry	2	2
ANL C, /bit	AND complement of direct bit to carry	2	2
ORL C, bit	OR direct bit to carry	2	2
ORL C, /bit	OR complement of direct bit to carry	2	2
MOV C, bit	Move direct bit to carry	2	2
MOV bit, C	Move carry to direct bit	2	3
JC rel	Jump if carry is set	2	3
JNC rel	Jump if no carry is set	2	3
JB bit, rel	Jump if direct bit is set	3	5
JNB bit, rel	Jump if direct bit is not set	3	5
JBC bit, rel	Jump if direct bit is set and clear bit	3	5

Figure 4-3. Interrupt Structure

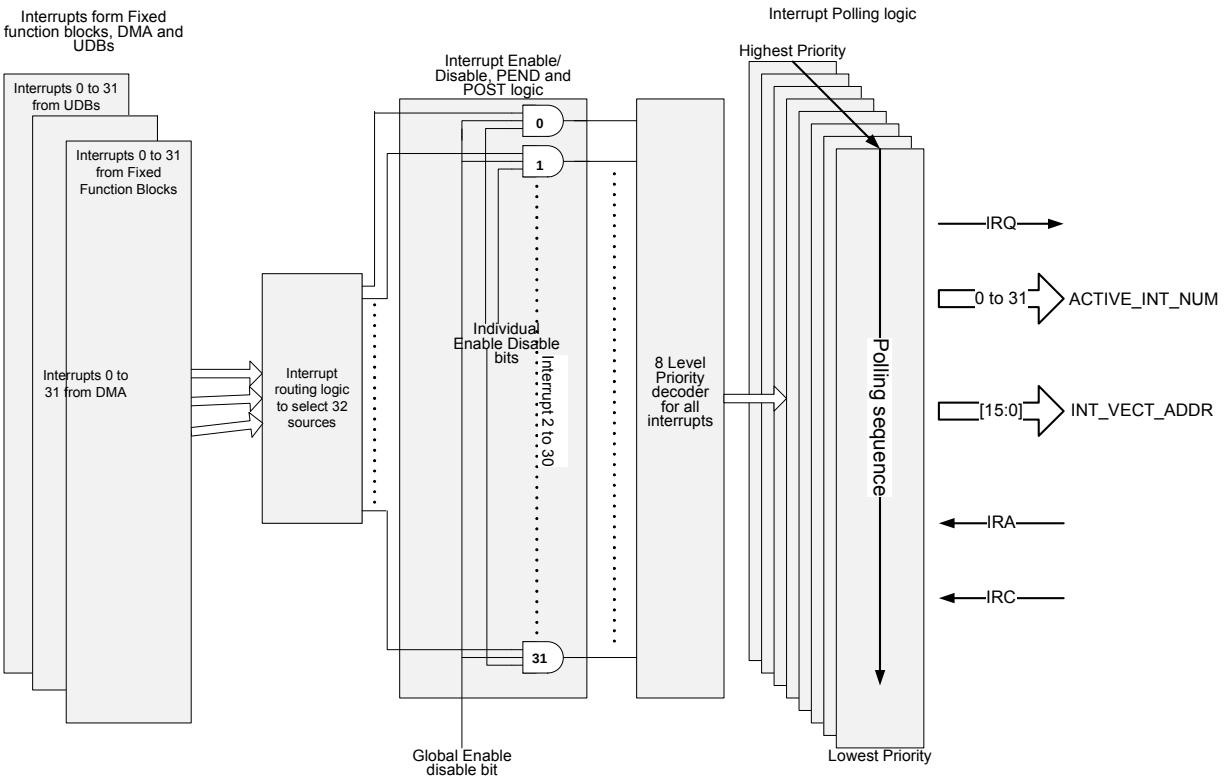


Table 4-8. Interrupt Vector Table

#	Fixed Function	DMA	UDB
0	LVD	phub_termout0[0]	udb_intr[0]
1	Cache/ECC	phub_termout0[1]	udb_intr[1]
2	Reserved	phub_termout0[2]	udb_intr[2]
3	Sleep (Pwr Mgr)	phub_termout0[3]	udb_intr[3]
4	PICU[0]	phub_termout0[4]	udb_intr[4]
5	PICU[1]	phub_termout0[5]	udb_intr[5]
6	PICU[2]	phub_termout0[6]	udb_intr[6]
7	PICU[3]	phub_termout0[7]	udb_intr[7]
8	PICU[4]	phub_termout0[8]	udb_intr[8]
9	PICU[5]	phub_termout0[9]	udb_intr[9]
10	PICU[6]	phub_termout0[10]	udb_intr[10]
11	PICU[12]	phub_termout0[11]	udb_intr[11]
12	PICU[15]	phub_termout0[12]	udb_intr[12]
13	Comparators Combined	phub_termout0[13]	udb_intr[13]
14	Switched Caps Combined	phub_termout0[14]	udb_intr[14]
15	I^2C	phub_termout0[15]	udb_intr[15]
16	CAN	phub_termout1[0]	udb_intr[16]
17	Timer/Counter0	phub_termout1[1]	udb_intr[17]
18	Timer/Counter1	phub_termout1[2]	udb_intr[18]
19	Timer/Counter2	phub_termout1[3]	udb_intr[19]
20	Timer/Counter3	phub_termout1[4]	udb_intr[20]
21	USB SOF Int	phub_termout1[5]	udb_intr[21]
22	USB Arb Int	phub_termout1[6]	udb_intr[22]

5.4 EEPROM

PSoC EEPROM memory is a byte-addressable nonvolatile memory. The CY8C36 has up to 2 KB of EEPROM memory to store user data. Reads from EEPROM are random access at the byte level. Reads are done directly; writes are done by sending write commands to an EEPROM programming interface. CPU code execution can continue from flash during EEPROM writes. EEPROM is erasable and writeable at the row level. The EEPROM is divided into 128 rows of 16 bytes each. The factory default values of all EEPROM bytes are 0.

Because the EEPROM is mapped to the 8051 xdata space, the CPU cannot execute out of EEPROM. There is no ECC hardware associated with EEPROM. If ECC is required it must be handled in firmware.

It can take as much as 20 milliseconds to write to EEPROM or flash. During this time the device should not be reset, or unexpected changes may be made to portions of EEPROM or flash. Reset sources (see *Section 6.3.1*) include XRES pin, software reset, and watchdog; care should be taken to make sure that these are not inadvertently activated. In addition, the low voltage detect circuits should be configured to generate an interrupt instead of a reset.

5.5 Nonvolatile Latches (NVLs)

PSoC has a 4-byte array of nonvolatile latches (NVLs) that are used to configure the device at reset. The NVL register map is shown in Table 5-2.

Table 5-2. Device Configuration NVL Register Map

Register Address	7	6	5	4	3	2	1	0
0x00	PRT3RDM[1:0]		PRT2RDM[1:0]		PRT1RDM[1:0]		PRT0RDM[1:0]	
0x01	PRT12RDM[1:0]		PRT6RDM[1:0]		PRT5RDM[1:0]		PRT4RDM[1:0]	
0x02	XRESMEN	DBGEN					PRT15RDM[1:0]	
0x03	DIG_PHS_DLY[3:0]				ECCEN	DPS[1:0]		CFGSPEED

The details for individual fields and their factory default settings are shown in Table 5-3.

Table 5-3. Fields and Factory Default Settings

Field	Description	Settings
PRTxRDM[1:0]	Controls reset drive mode of the corresponding IO port. See "Reset Configuration" on page 43. All pins of the port are set to the same mode.	00b (default) - high impedance analog 01b - high impedance digital 10b - resistive pull up 11b - resistive pull down
XRESMEN	Controls whether pin P1[2] is used as a GPIO or as an external reset. See "Pin Descriptions" on page 12, XRES description.	0 (default for 68-pin 72-pin, and 100-pin parts) - GPIO 1 (default for 48-pin parts) - external reset
DBGEN	Debug Enable allows access to the debug system, for third-party programmers.	0 - access disabled 1 (default) - access enabled
CFGSPEED	Controls the speed of the IMO-based clock during the device boot process, for faster boot or low-power operation	0 (default) - 12 MHz IMO 1 - 48 MHz IMO
DPS[1:0]	Controls the usage of various P1 pins as a debug port. See "Programming, Debug Interfaces, Resources" on page 65.	00b - 5-wire JTAG 01b (default) - 4-wire JTAG 10b - SWD 11b - debug ports disabled
ECCEN	Controls whether ECC flash is used for ECC or for general configuration and data storage. See "Flash Program Memory" on page 23.	0 - ECC disabled 1 (default) - ECC enabled
DIG_PHS_DLY[3:0]	Selects the digital clock phase delay.	See the TRM for details.

Although PSoC Creator provides support for modifying the device configuration NVLs, the number of NVL erase / write cycles is limited – see "Nonvolatile Latches (NVL))" on page 110.

6. System Integration

6.1 Clocking System

The clocking system generates, divides, and distributes clocks throughout the PSoC system. For the majority of systems, no external crystal is required. The IMO and PLL together can generate up to a 66 MHz clock, accurate to ±1% over voltage and temperature. Additional internal and external clock sources allow each design to optimize accuracy, power, and cost. Any of the clock sources can be used to generate other clock frequencies in the 16-bit clock dividers and UDBs for anything the user wants, for example a UART baud rate generator.

Clock generation and distribution is automatically configured through the PSoC Creator IDE graphical interface. This is based on the complete system's requirements. It greatly speeds the design process. PSoC Creator allows you to build clocking systems with minimal input. You can specify desired clock frequencies and accuracies, and the software locates or builds a clock that meets the required specifications. This is possible because of the programmability inherent in PSoC.

Key features of the clocking system include:

- Seven general purpose clock sources
  - 3- to 62-MHz IMO, ±1% at 3 MHz
  - 4- to 25-MHz external crystal oscillator (MHzECO)
  - Clock doubler provides a doubled clock frequency output for the USB block, see USB Clock Domain on page 30.
  - DSI signal from an external I/O pin or other logic
  - 24- to 67-MHz fractional PLL sourced from IMO, MHzECO, or DSI
  - 1-kHz, 33-kHz, 100-kHz ILO for WDT and sleep timer
  - 32.768-kHz external crystal oscillator (kHzECO) for RTC
- IMO has a USB mode that auto locks to the USB bus clock requiring no external crystal for USB. (USB equipped parts only)
- Independently sourced clock in all clock dividers
- Eight 16-bit clock dividers for the digital system
- Four 16-bit clock dividers for the analog system
- Dedicated 16-bit divider for the bus clock
- Dedicated 4-bit divider for the CPU clock
- Automatic clock configuration in PSoC Creator

Figure 6-1. Clocking Subsystem

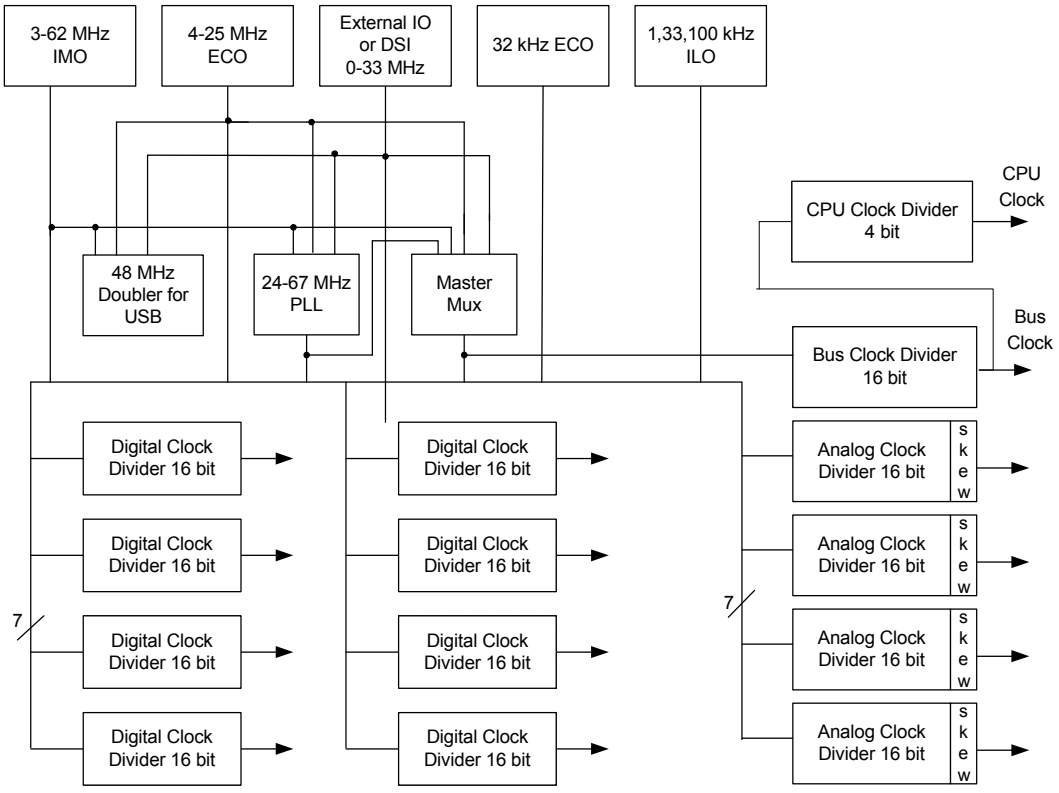


Figure 6-10. SIO Input/Output Block Diagram

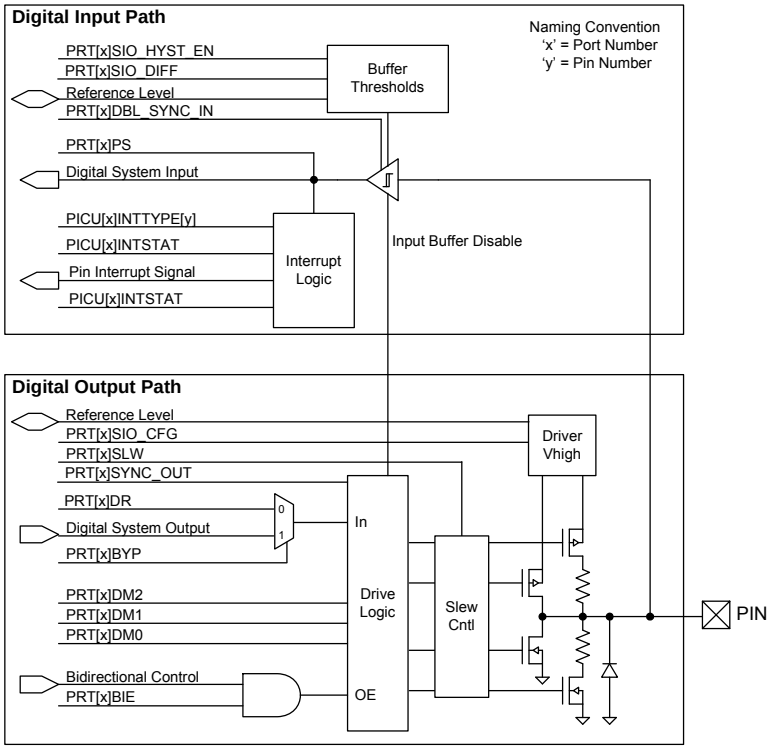
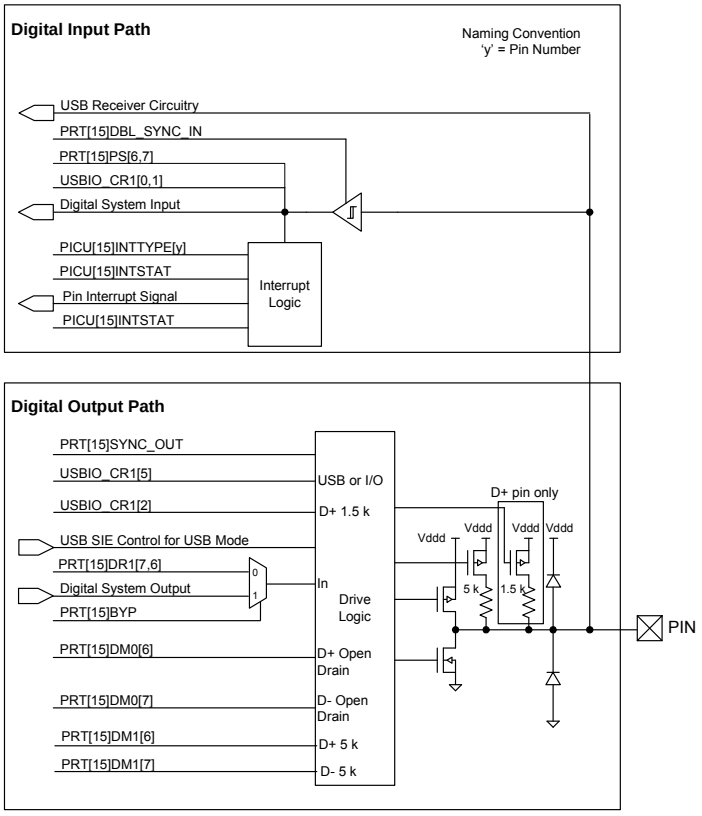


Figure 6-11. USBIO Block Diagram



9.2 Serial Wire Debug Interface

The SWD interface is the preferred alternative to the JTAG interface. It requires only two pins instead of the four or five needed by JTAG. SWD provides all of the programming and debugging features of JTAG at the same speed. SWD does not provide access to scan chains or device chaining. The SWD clock frequency can be up to 1/3 of the CPU clock frequency.

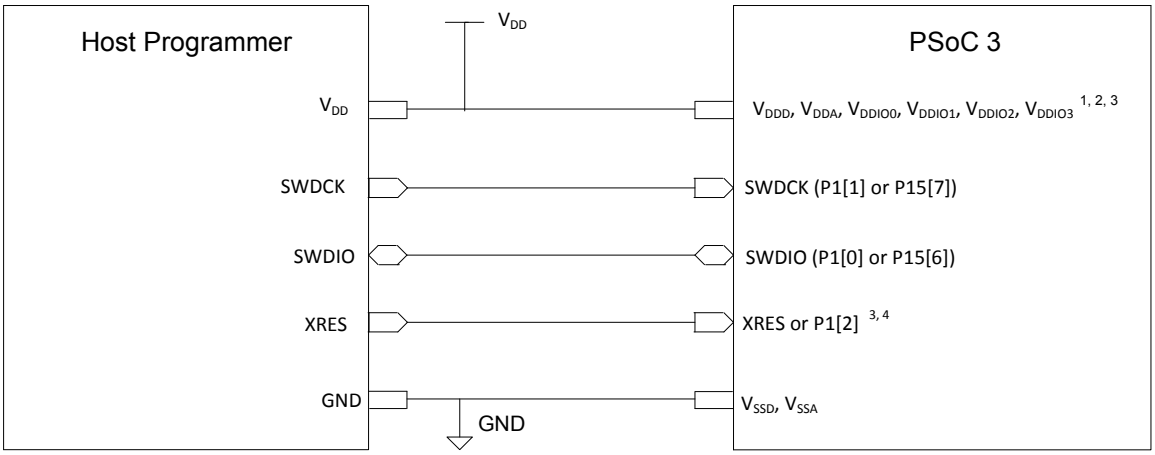
SWD uses two pins, either two of the JTAG pins (TMS and TCK) or the USBIO D+ and D– pins. The USBIO pins are useful for in system programming of USB solutions that would otherwise require a separate programming connector. One pin is used for the data clock and the other is used for data input and output.

SWD can be enabled on only one of the pin pairs at a time. This only happens if, within 8 µs (key window) after reset, that pin pair (JTAG or USB) receives a predetermined acquire sequence of 1s and 0s. If the NVL latches are set for SWD (see *Section 5.5*), this sequence need not be applied to the JTAG pin pair. The acquire sequence must always be applied to the USB pin pair.

SWD is used for debugging or for programming the flash memory.

The SWD interface can be enabled from the JTAG interface or disabled, allowing its pins to be used as GPIO. Unlike JTAG, the SWD interface can always be reacquired on any device during the key window. It can then be used to reenable the JTAG interface, if desired. When using SWD or JTAG pins as standard GPIO, make sure that the GPIO functionality and PCB circuits do not interfere with SWD or JTAG use.

Figure 9-2. SWD Interface Connections between PSoC 3 and Programmer



[1] The voltage levels of the Host Programmer and the PSoC 3 voltage domains involved in Programming should be the same. XRES pin (XRES_N or P1[2]) is powered by V_{DDIO1}. The USB SWD pins are powered by V_{DDD}. So for Programming using the USB SWD pins with XRES pin, the V_{DDD}, V_{DDIO1} of PSoC 3 should be at the same voltage level as Host V_{DD}. Rest of PSoC 3 voltage domains (V_{DDA}, V_{DDIO0}, V_{DDIO2}, V_{DDIO3}) need not be at the same voltage level as host Programmer. The Port 1 SWD pins are powered by V_{DDIO1}. So V_{DDIO1} of PSoC 3 should be at same voltage level as host V_{DD} for Port 1 SWD programming. Rest of PSoC 3 voltage domains (V_{DDD}, V_{DDA}, V_{DDIO0}, V_{DDIO2}, V_{DDIO3}) need not be at the same voltage level as host Programmer.

[2] Vdda must be greater than or equal to all other power supplies (Vddd, Vddio's) in PSoC 3.

[3] For Power cycle mode Programming, XRES pin is not required. But the Host programmer must have the capability to toggle power (Vddd, Vdda, All Vddio's) to PSoC 3. This may typically require external interface circuitry to toggle power which will depend on the programming setup. The power supplies can be brought up in any sequence, however, once stable, VDDA must be greater than or equal to all other supplies.

[4] P1[2] will be configured as XRES by default only for 48-pin devices (without dedicated XRES pin). For devices with dedicated XRES pin, P1[2] is GPIO pin by default. So use P1[2] as Reset pin only for 48-pin devices, but use dedicated XRES pin for rest of devices.

9.3 Debug Features

Using the JTAG or SWD interface, the CY8C36 supports the following debug features:

- Halt and single-step the CPU
- View and change CPU and peripheral registers, and RAM addresses
- Eight program address breakpoints
- One memory access breakpoint—break on reading or writing any memory address and data value
- Break on a sequence of breakpoints (non recursive)
- Debugging at the full speed of the CPU
- Compatible with PSoC Creator and MiniProg3 programmer and debugger
- Standard JTAG programming and debugging interfaces make CY8C36 compatible with other popular third-party tools (for example, ARM / Keil)

9.4 Trace Features

The CY8C36 supports the following trace features when using JTAG or SWD:

- Trace the 8051 program counter (PC), accumulator register (ACC), and one SFR / 8051 core RAM register
- Trace depth up to 1000 instructions if all registers are traced, or 2000 instructions if only the PC is traced (on devices that include trace memory)
- Program address trigger to start tracing
- Trace windowing, that is, only trace when the PC is within a given range
- Two modes for handling trace buffer full: continuous (overwriting the oldest trace data) or break when trace buffer is full

9.5 Single Wire Viewer Interface

The SWV interface is closely associated with SWD but can also be used independently. SWV data is output on the JTAG interface's TDO pin. If using SWV, you must configure the device for SWD, not JTAG. SWV is not supported with the JTAG interface.

SWV is ideal for application debug where it is helpful for the firmware to output data similar to 'printf' debugging on PCs. The SWV is ideal for data monitoring, because it requires only a single pin and can output data in standard UART format or Manchester encoded format. For example, it can be used to tune a PID control loop in which the output and graphing of the three error terms greatly simplifies coefficient tuning.

The following features are supported in SWV:

- 32 virtual channels, each 32 bits long
- Simple, efficient packing and serializing protocol
- Supports standard UART format (N81)

9.6 Programming Features

The JTAG and SWD interfaces provide full programming support. The entire device can be erased, programmed, and verified. You can increase flash protection levels to protect firmware IP. Flash protection can only be reset after a full device erase. Individual flash blocks can be erased, programmed, and verified, if block security settings permit.

9.7 Device Security

PSoC 3 offers an advanced security feature called device security, which permanently disables all test, programming, and debug ports, protecting your application from external access. The device security is activated by programming a 32-bit key (0×50536F43) to a Write Once Latch (WOL).

The WOL is a type of nonvolatile latch (NVL). The cell itself is an NVL with additional logic wrapped around it. Each WOL device contains four bytes (32 bits) of data. The wrapper outputs a '1' if a super-majority (28 of 32) of its bits match a pre-determined pattern (0×50536F43); it outputs a '0' if this majority is not reached. When the output is 1, the Write Once NV latch locks the part out of Debug and Test modes; it also permanently gates off the ability to erase or alter the contents of the latch. Matching all bits is intentionally not required, so that single (or few) bit failures do not deassert the WOL output. The state of the NVL bits after wafer processing is truly random with no tendency toward 1 or 0.

The WOL only locks the part after the correct 32-bit key (0×50536F43) is loaded into the NVL's volatile memory, programmed into the NVL's nonvolatile cells, and the part is reset. The output of the WOL is only sampled on reset and used to disable the access. This precaution prevents anyone from reading, erasing, or altering the contents of the internal memory.

The user can write the key into the WOL to lock out external access only if no flash protection is set (see "Flash Security" on page 23). However, after setting the values in the WOL, a user still has access to the part until it is reset. Therefore, a user can write the key into the WOL, program the flash protection data, and then reset the part to lock it.

If the device is protected with a WOL setting, Cypress cannot perform failure analysis and, therefore, cannot accept RMAs from customers. The WOL can be read out through the SWD port to electrically identify protected parts. The user can write the key in WOL to lock out external access only if no flash protection is set. For more information on how to take full advantage of the security features in PSoC see the PSoC 3 TRM.

Disclaimer

Note the following details of the flash code protection features on Cypress devices.

Cypress products meet the specifications contained in their particular Cypress data sheets. Cypress believes that its family of products is one of the most secure families of its kind on the market today, regardless of how they are used. There may be methods, unknown to Cypress, that can breach the code protection features. Any of these methods, to our knowledge, would be dishonest and possibly illegal. Neither Cypress nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Cypress is willing to work with the customer who is concerned about the integrity of their code. Code protection is constantly evolving. We at Cypress are committed to continuously improving the code protection features of our products.

Figure 11-11. Efficiency vs V_{BAT}, L_{BOOST} = 4.7 µH [42]

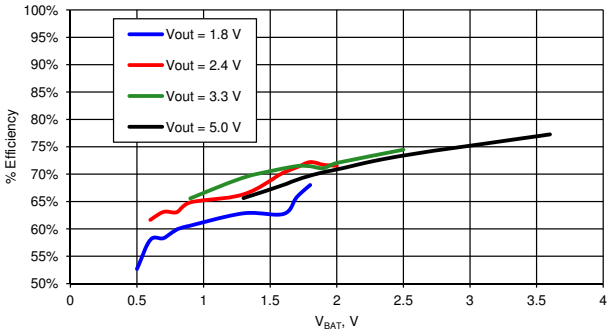


Figure 11-12. Efficiency vs V_{BAT}, L_{BOOST} = 10 µH [42]

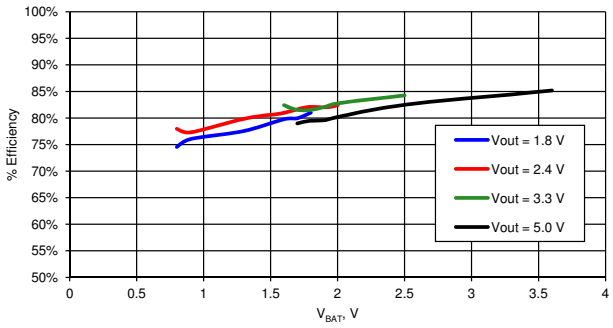


Figure 11-13. Efficiency vs V_{BAT}, L_{BOOST} = 22 µH [42]

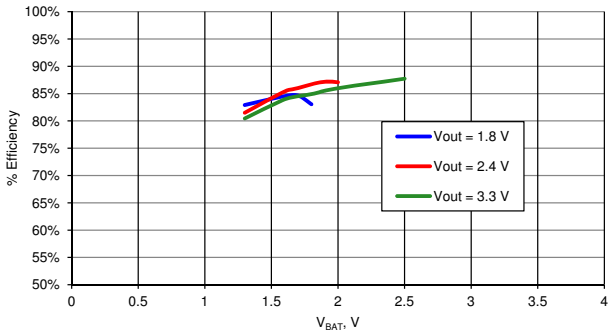
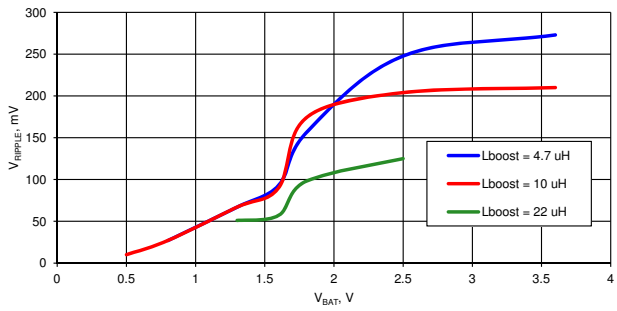


Figure 11-14. V_{RIPPLE} vs V_{BAT} [42]



Note
42. Typical example. Actual values may vary depending on external component selection, PCB layout, and other design parameters.

11.4 Inputs and Outputs

Specifications are valid for –40 °C ≤ T_A ≤ 85 °C and T_J ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted. Unless otherwise specified, all charts and graphs show typical values.

When the power supplies ramp up, there are low-impedance connections between each GPIO pin and its V_{DDIO} supply. This causes the pin voltages to track V_{DDIO} until both V_{DDIO} and V_{DDA} reach the IPOR voltage, which can be as high as 1.45 V. At that point, the low-impedance connections no longer exist and the pins change to their normal NVL settings.

11.4.1 GPIO

Table 11-9. GPIO DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
V_{IH}	Input voltage high threshold	CMOS Input, PRT[×]CTL = 0	0.7 × V_{DDIO}	–	–	V
V_{IL}	Input voltage low threshold	CMOS Input, PRT[×]CTL = 0	–	–	0.3 × V_{DDIO}	V
V_{IH}	Input voltage high threshold	LVTTL Input, PRT[×]CTL = 1,V_{DDIO} < 2.7 V	0.7 × V_{DDIO}	–	–	V
V_{IH}	Input voltage high threshold	LVTTL Input, PRT[×]CTL = 1, V_{DDIO} ≥ 2.7 V	2.0	–	–	V
V_{IL}	Input voltage low threshold	LVTTL Input, PRT[×]CTL = 1,V_{DDIO} < 2.7 V	–	–	0.3 × V_{DDIO}	V
V_{IL}	Input voltage low threshold	LVTTL Input, PRT[×]CTL = 1, V_{DDIO} ≥ 2.7 V	–	–	0.8	V
V_{OH}	Output voltage high	I_{OH} = 4 mA at 3.3 V_{DDIO}	V_{DDIO} – 0.6	–	–	V
		I_{OH} = 1 mA at 1.8 V_{DDIO}	V_{DDIO} – 0.5	–	–	V
V_{OL}	Output voltage low	I_{OL} = 8 mA at 3.3 V_{DDIO}	–	–	0.6	V
		I_{OL} = 4 mA at 1.8 V_{DDIO}	–	–	0.6	V
		I_{OL} = 3 mA at 3.3 V_{DDIO}	–	–	0.4	V
Rpullup	Pull-up resistor		3.5	5.6	8.5	kΩ
Rpulldown	Pull-down resistor		3.5	5.6	8.5	kΩ
I_{IL}	Input leakage current (absolute value)[43]	25 °C, V_{DDIO} = 3.0 V	–	–	2	nA
C_{IN}	Input capacitance[43]	GPIOs not shared with opamp outputs, MHz ECO or kHzECO	–	4	7	pF
		GPIOs shared with MHz ECO or kHzECO[44]	–	5	7	pF
		GPIOs shared with opamp outputs	–	–	18	pF
V_H	Input voltage hysteresis (Schmitt-Trigger)[43]		–	40	–	mV
Idiode	Current through protection diode to V_{DDIO} and V_{SSIO}		–	–	100	µA
Rglobal	Resistance pin to analog global bus	25 °C, V_{DDIO} = 3.0 V	–	320	–	Ω
Rmux	Resistance pin to analog mux bus	25 °C, V_{DDIO} = 3.0 V	–	220	–	Ω

Notes
43. Based on device characterization (Not production tested).
44. For information on designing with PSoC oscillators, refer to the application note, AN54439 - PSoC® 3 and PSoC 5 External Oscillator.

11.4.2 SIO

Table 11-11. SIO DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
Vinmax	Maximum input voltage	All allowed values of V_{DDIO} and V_{DDD}, see *Section 11.1*	–	–	5.5	V
Vinref	Input voltage reference (Differential input mode)		0.5	–	$0.52 \times V_{DDIO}$	V
Voutref	Output voltage reference (Regulated output mode)					
		$V_{DDIO} > 3.7$	1	–	$V_{DDIO} - 1$	V
		$V_{DDIO} < 3.7$	1	–	$V_{DDIO} - 0.5$	V
V_{IH}	Input voltage high threshold					
	GPIO mode	CMOS input	$0.7 \times V_{DDIO}$	–	–	V
	Differential input mode[46]	Hysteresis disabled	SIO_ref + 0.2	–	–	V
V_{IL}	Input voltage low threshold					
	GPIO mode	CMOS input	–	–	$0.3 \times V_{DDIO}$	V
	Differential input mode[46]	Hysteresis disabled	–	–	SIO_ref – 0.2	V
V_{OH}	Output voltage high					
	Unregulated mode	I_{OH} = 4 mA, V_{DDIO} = 3.3 V	$V_{DDIO} - 0.4$	–	–	V
	Regulated mode[46]	I_{OH} = 1 mA	SIO_ref – 0.65	–	SIO_ref + 0.2	V
	Regulated mode[46]	I_{OH} = 0.1 mA	SIO_ref – 0.3	–	SIO_ref + 0.2	V
V_{OL}	Output voltage low	V_{DDIO} = 3.30 V, I_{OL} = 25 mA	–	–	0.8	V
		V_{DDIO} = 3.30 V, I_{OL} = 20 mA	–	–	0.4	V
		V_{DDIO} = 1.80 V, I_{OL} = 4 mA	–	–	0.4	V
Rpullup	Pull-up resistor		3.5	5.6	8.5	kΩ
Rpulldown	Pull-down resistor		3.5	5.6	8.5	kΩ
I_{IL}	Input leakage current (absolute value)[47]		–	–	–	–
	$V_{IH} \leq$ Vddsio	25 °C, Vddsio = 3.0 V, V_{IH} = 3.0 V	–	–	14	nA
	V_{IH} > Vddsio	25 °C, Vddsio = 0 V, V_{IH} = 3.0 V	–	–	10	µA
C_{IN}	Input Capacitance[47]		–	–	7	pF
V_H	Input voltage hysteresis (Schmitt-Trigger)[47]	Single ended mode (GPIO mode)	–	40	–	mV
		Differential mode	–	35	–	mV
Idiode	Current through protection diode to V_{SSIO}		–	–	100	µA

Notes
46. See Figure 6-10 on page 39 and Figure 6-13 on page 43 for more information on SIO reference.
47. Based on device characterization (Not production tested)

Table 11-12. SIO AC Specifications *(continued)*

Parameter	Description	Conditions	Min	Typ	Max	Units
Fsioout	SIO output operating frequency					
	2.7 V < V_{DDIO} < 5.5 V, Unregulated output (GPIO) mode, fast strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	33	MHz
	1.71 V < V_{DDIO} < 2.7 V, Unregulated output (GPIO) mode, fast strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	16	MHz
	3.3 V < V_{DDIO} < 5.5 V, Unregulated output (GPIO) mode, slow strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	5	MHz
	1.71 V < V_{DDIO} < 3.3 V, Unregulated output (GPIO) mode, slow strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	4	MHz
	2.7 V < V_{DDIO} < 5.5 V, Regulated output mode, fast strong drive mode	Output continuously switching into 25 pF	–	–	20	MHz
	1.71 V < V_{DDIO} < 2.7 V, Regulated output mode, fast strong drive mode	Output continuously switching into 25 pF	–	–	10	MHz
	1.71 V < V_{DDIO} < 5.5 V, Regulated output mode, slow strong drive mode	Output continuously switching into 25 pF	–	–	2.5	MHz
Fsioin	SIO input operating frequency					
	1.71 V ≤ V_{DDIO} ≤ 5.5 V	90/10% V_{DDIO}	–	–	33	MHz

Figure 11-20. SIO Output Rise and Fall Times, Fast Strong Mode, V_{DDIO} = 3.3 V, 25 pF Load

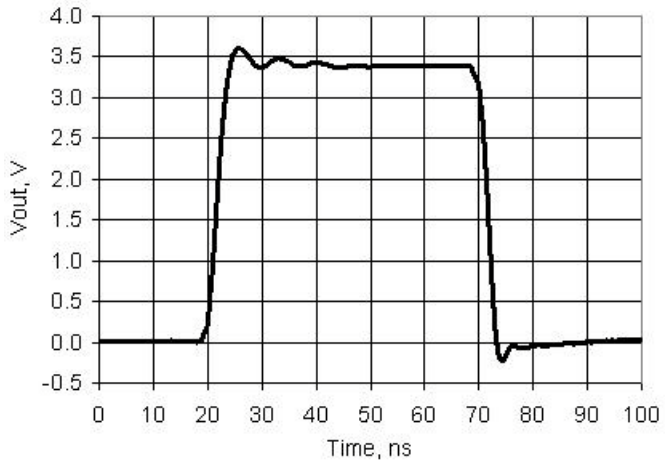


Figure 11-21. SIO Output Rise and Fall Times, Slow Strong Mode, V_{DDIO} = 3.3 V, 25 pF Load

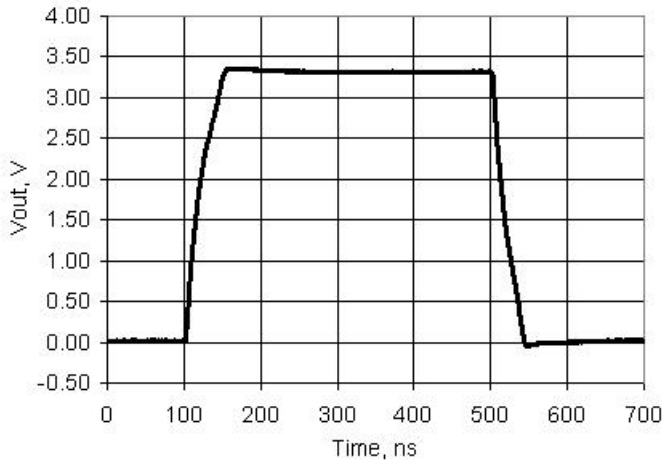


Table 11-13. SIO Comparator Specifications[49]

Parameter	Description	Conditions	Min	Typ	Max	Units
Vos	Offset voltage	V_{DDIO} = 2 V	–	–	68	mV
		V_{DDIO} = 2.7 V	–	–	72	
		V_{DDIO} = 5.5 V	–	–	82	
TCVos	Offset voltage drift with temp		–	–	250	µV/°C
CMRR	Common mode rejection ratio	V_{DDIO} = 2 V	30	–	–	dB
		V_{DDIO} = 2.7 V	35	–	–	
		V_{DDIO} = 5.5 V	40	–	–	
Tresp	Response time		–	–	30	ns

11.4.3 USBIO

For operation in GPIO mode, the standard range for V_{DDD} applies, see Device Level Specifications on page 72.

Table 11-14. USBIO DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
Rusbi	USB D+ pull-up resistance	With idle bus	0.900	–	1.575	kΩ
Rusba	USB D+ pull-up resistance	While receiving traffic	1.425	–	3.090	kΩ
Vohusb	Static output high	15 kΩ ±5% to Vss, internal pull-up enabled	2.8	–	3.6	V
Volusb	Static output low	15 kΩ ±5% to Vss, internal pull-up enabled	–	–	0.3	V
Vihgpio	Input voltage high, GPIO mode	$V_{DDD} \geq 3$ V	2	–	–	V
Vilgpio	Input voltage low, GPIO mode	$V_{DDD} \geq 3$ V	–	–	0.8	V
Vohgpio	Output voltage high, GPIO mode	I_{OH} = 4 mA, $V_{DDD} \geq 3$ V	2.4	–	–	V
Volgpio	Output voltage low, GPIO mode	I_{OL} = 4 mA, $V_{DDD} \geq 3$ V	–	–	0.3	V
Vdi	Differential input sensitivity	|(D+)–(D–)|	–	–	0.2	V
Vcm	Differential input common mode range	–	0.8	–	2.5	V
Vse	Single ended receiver threshold	–	0.8	–	2	V
Rps2	PS/2 pull-up resistance	In PS/2 mode, with PS/2 pull-up enabled	3	–	7	kΩ
Rext	External USB series resistor	In series with each USB pin	21.78 (–1%)	22	22.22 (+1%)	Ω
Zo	USB driver output impedance	Including Rext	28	–	44	Ω
C_{IN}	USB transceiver input capacitance		–	–	20	pF
I_{IL}[49]	Input leakage current (absolute value)	25 °C, V_{DDD} = 3.0 V	–	–	2	nA

Note
49. Based on device characterization (Not production tested).

11.4.4 XRES

Table 11-17. XRES DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
V_{IH}	Input voltage high threshold		0.7 × V_{DDIO}	–	–	V
V_{IL}	Input voltage low threshold		–	–	0.3 × V_{DDIO}	V
Rpullup	Pull-up resistor		3.5	5.6	8.5	kΩ
C_{IN}	Input capacitance[50]		–	3	–	pF
V_H	Input voltage hysteresis (Schmitt–Trigger)[50]		–	100	–	mV
Idiode	Current through protection diode to V_{DDIO} and V_{SSIO}		–	–	100	µA

Table 11-18. XRES AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
T_{RESET}	Reset pulse width		1	–	–	µs

11.5 Analog Peripherals

Specifications are valid for –40 °C ≤ T_A ≤ 85 °C and T_J ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

11.5.1 Opamp

Table 11-19. Opamp DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
V_{IOFF}	Input offset voltage		–	–	2	mV
V_{OS}	Input offset voltage		–	–	2.5	mV
		Operating temperature –40 °C to 70 °C	–	–	2	mV
TCV_{OS}	Input offset voltage drift with temperature	Power mode = high	–	–	±30	µV / °C
Ge1	Gain error, unity gain buffer mode	Rload = 1 kΩ	–	–	±0.1	%
C_{IN}	Input capacitance	Routing from pin	–	–	18	pF
V_O	Output voltage range	1 mA, source or sink, power mode = high	V_{SSA} + 0.05	–	V_{DDA} – 0.05	V
I_{OUT}	Output current capability, source or sink	V_{SSA} + 500 mV ≤ Vout ≤ V_{DDA} –500 mV, V_{DDA} > 2.7 V	25	–	–	mA
		V_{SSA} + 500 mV ≤ Vout ≤ V_{DDA} –500 mV, 1.7 V = V_{DDA} ≤ 2.7 V	16	–	–	mA
I_{DD}	Quiescent current	Power mode = min	–	250	400	uA
		Power mode = low	–	250	400	uA
		Power mode = med	–	330	950	uA
		Power mode = high	–	1000	2500	uA
CMRR	Common mode rejection ratio		80	–	–	dB
PSRR	Power supply rejection ratio	V_{DDA} ≥ 2.7 V	85	–	–	dB
		V_{DDA} < 2.7 V	70	–	–	dB
I_{IB}	Input bias current[50]	25 °C	–	10	–	pA

Note
50. Based on device characterization (Not production tested).

Table 11-28. IDAC DC Specifications *(continued)*

Parameter	Description	Conditions	Min	Typ	Max	Units
Ezs	Zero scale error		–	0	±1	LSB
Eg	Gain error	Range = 2.04 mA, 25 °C	–	–	±2.5	%
		Range = 255 µA, 25 ° C	–	–	±2.5	%
		Range = 31.875 µA, 25 ° C	–	–	±3.5	%
TC_Eg	Temperature coefficient of gain error	Range = 2.04 mA	–	–	0.04	% / °C
		Range = 255 µA	–	–	0.04	% / °C
		Range = 31.875 µA	–	–	0.05	% / °C
INL	Integral nonlinearity	Sink mode, range = 255 µA, Codes 8 – 255, Rload = 2.4 kΩ, Cload = 15 pF	–	±0.9	±1	LSB
		Source mode, range = 255 µA, Codes 8 – 255, Rload = 2.4 kΩ, Cload = 15 pF	–	±1.2	±1.6	LSB
DNL	Differential nonlinearity	Sink mode, range = 255 µA, Rload = 2.4 kΩ, Cload = 15 pF	–	±0.3	±1	LSB
		Source mode, range = 255 µA, Rload = 2.4 kΩ, Cload = 15 pF	–	±0.3	±1	LSB
Vcompliance	Dropout voltage, source or sink mode	Voltage headroom at max current, Rload to V_{DDA} or Rload to V_{SSA}, V_{DIFF} from V_{DDA}	1	–	–	V
I_{DD}	Operating current, code = 0	Low speed mode, source mode, range = 31.875 µA	–	44	100	µA
		Low speed mode, source mode, range = 255 µA,	–	33	100	µA
		Low speed mode, source mode, range = 2.04 mA	–	33	100	µA
		Low speed mode, sink mode, range = 31.875 µA	–	36	100	µA
		Low speed mode, sink mode, range = 255 µA	–	33	100	µA
		Low speed mode, sink mode, range = 2.04 mA	–	33	100	µA
		High speed mode, source mode, range = 31.875 µA	–	310	500	µA
		High speed mode, source mode, range = 255 µA	–	305	500	µA
		High speed mode, source mode, range = 2.04 mA	–	305	500	µA
		High speed mode, sink mode, range = 31.875 µA	–	310	500	µA
		High speed mode, sink mode, range = 255 µA	–	300	500	µA
		High speed mode, sink mode, range = 2.04 mA	–	300	500	µA

11.6.8 Universal Digital Blocks (UDBs)

PSoC Creator provides a library of prebuilt and tested standard digital peripherals (UART, SPI, LIN, PRS, CRC, timer, counter, PWM, AND, OR, and so on) that are mapped to the UDB array. See the component data sheets in PSoC Creator for full AC/DC specifications, APIs, and example code.

Table 11-54. UDB AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
Datapath Performance						
F_{MAX_TIMER}	Maximum frequency of 16-bit timer in a UDB pair		–	–	67.01	MHz
F_{MAX_ADDER}	Maximum frequency of 16-bit adder in a UDB pair		–	–	67.01	MHz
F_{MAX_CRC}	Maximum frequency of 16-bit CRC/PRS in a UDB pair		–	–	67.01	MHz
PLD Performance						
F_{MAX_PLD}	Maximum frequency of a two-pass PLD function in a UDB pair		–	–	67.01	MHz
Clock to Output Performance						
t_{CLK_OUT}	Propagation delay for clock in to data out, see Figure 11-65.	25 °C, $V_{DDD} \geq 2.7$ V	–	20	25	ns
t_{CLK_OUT}	Propagation delay for clock in to data out, see Figure 11-65.	Worst-case placement, routing, and pin selection	–	–	55	ns

Figure 11-65. Clock to Output Performance

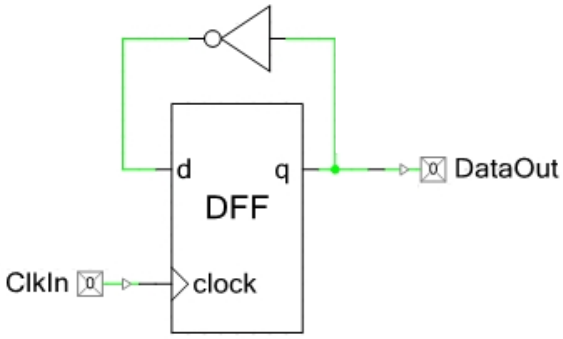


Figure 13-1. 48-pin (300 mil) SSOP Package Outline

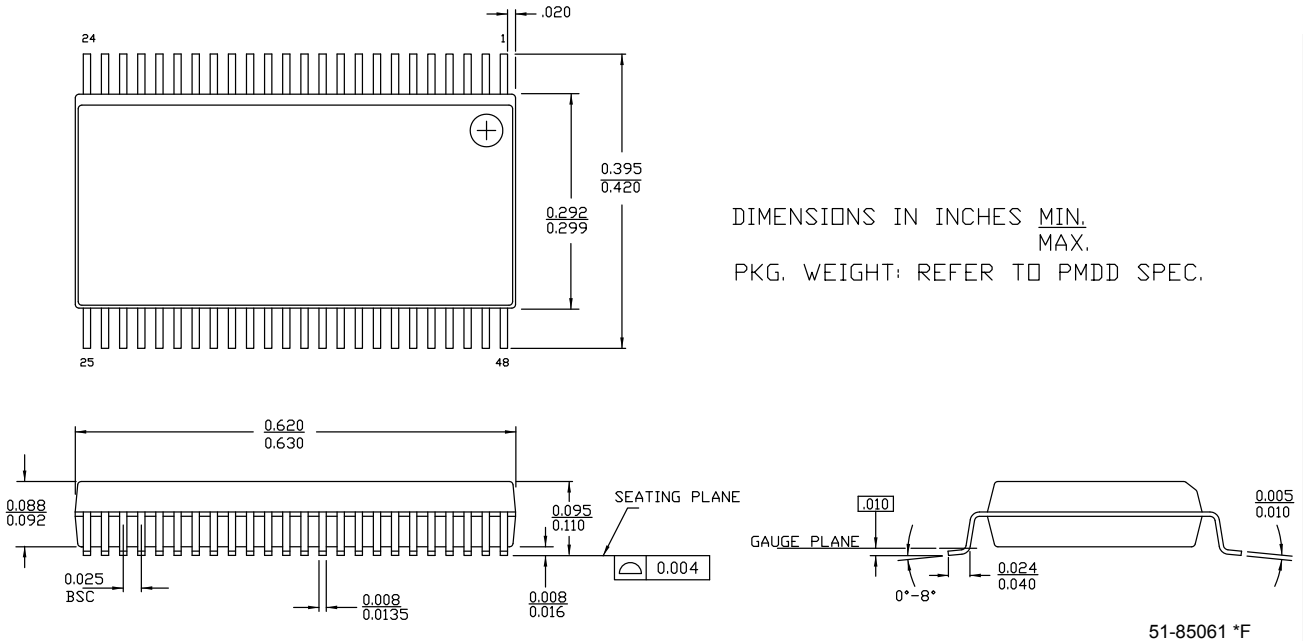
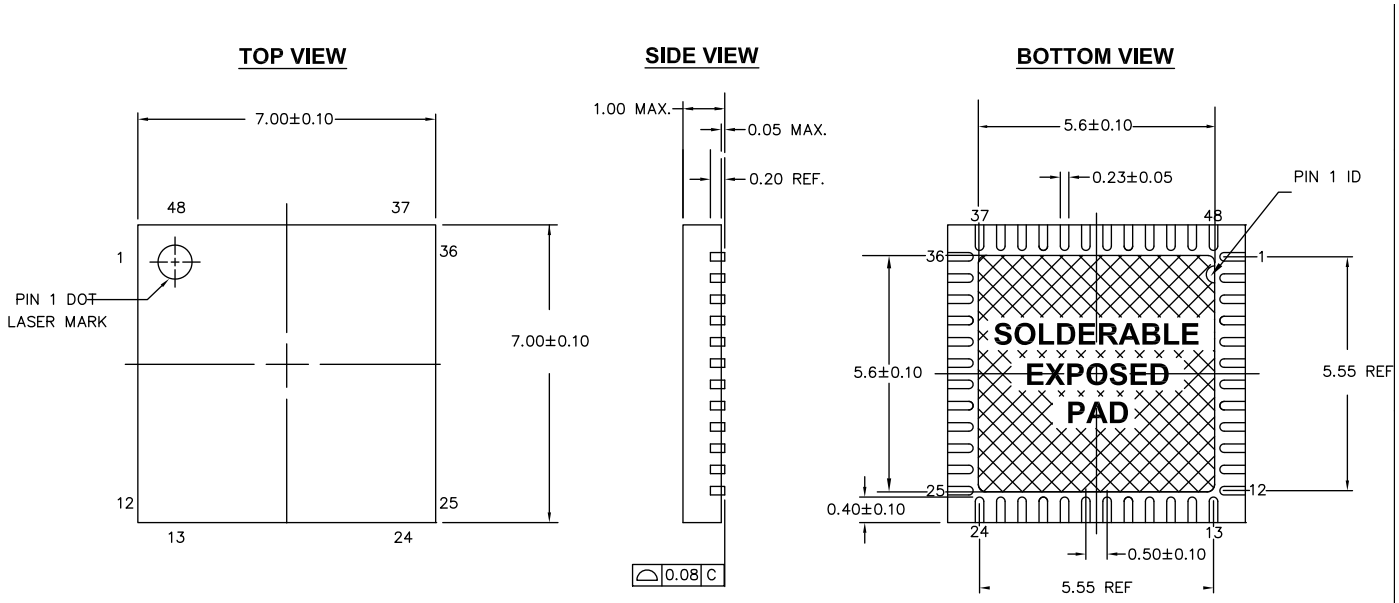


Figure 13-2. 48-pin QFN Package Outline



NOTES:

1. ▨ HATCH AREA IS SOLDERABLE EXPOSED METAL.
2. REFERENCE JEDEC#: MO-220
3. PACKAGE WEIGHT: REFER TO PMDD SPEC.
4. ALL DIMENSIONS ARE IN MM [MIN/MAX]
5. PACKAGE CODE

PART #	DESCRIPTION
LT48D	LEAD FREE

001-45616 *E

14. Acronyms

Table 14-1. Acronyms Used in this Document

Acronym	Description
abus	analog local bus
ADC	analog-to-digital converter
AG	analog global
AHB	AMBA (advanced microcontroller bus architecture) high-performance bus, an ARM data transfer bus
ALU	arithmetic logic unit
AMUXBUS	analog multiplexer bus
API	application programming interface
APSR	application program status register
ARM®	advanced RISC machine, a CPU architecture
ATM	automatic thump mode
BW	bandwidth
CAN	Controller Area Network, a communications protocol
CMRR	common-mode rejection ratio
CPU	central processing unit
CRC	cyclic redundancy check, an error-checking protocol
DAC	digital-to-analog converter, see also IDAC, VDAC
DFB	digital filter block
DIO	digital input/output, GPIO with only digital capabilities, no analog. See GPIO.
DMA	direct memory access, see also TD
DNL	differential nonlinearity, see also INL
DNU	do not use
DR	port write data registers
DSI	digital system interconnect
DWT	data watchpoint and trace
ECC	error correcting code
ECO	external crystal oscillator
EEPROM	electrically erasable programmable read-only memory
EMI	electromagnetic interference
EMIF	external memory interface
EOC	end of conversion
EOF	end of frame
EPSR	execution program status register
ESD	electrostatic discharge
ETM	embedded trace macrocell

Table 14-1. Acronyms Used in this Document *(continued)*

Acronym	Description
FIR	finite impulse response, see also IIR
FPB	flash patch and breakpoint
FS	full-speed
GPIO	general-purpose input/output, applies to a PSoC pin
HVI	high-voltage interrupt, see also LVI, LVD
IC	integrated circuit
IDAC	current DAC, see also DAC, VDAC
IDE	integrated development environment
I^2C, or IIC	Inter-Integrated Circuit, a communications protocol
IIR	infinite impulse response, see also FIR
ILO	internal low-speed oscillator, see also IMO
IMO	internal main oscillator, see also ILO
INL	integral nonlinearity, see also DNL
I/O	input/output, see also GPIO, DIO, SIO, USBIO
IPOR	initial power-on reset
IPSR	interrupt program status register
IRQ	interrupt request
ITM	instrumentation trace macrocell
LCD	liquid crystal display
LIN	Local Interconnect Network, a communications protocol.
LR	link register
LUT	lookup table
LVD	low-voltage detect, see also LVI
LVI	low-voltage interrupt, see also HVI
LVTTL	low-voltage transistor-transistor logic
MAC	multiply-accumulate
MCU	microcontroller unit
MISO	master-in slave-out
NC	no connect
NMI	nonmaskable interrupt
NRZ	non-return-to-zero
NVIC	nested vectored interrupt controller
NVL	nonvolatile latch, see also WOL
opamp	operational amplifier
PAL	programmable array logic, see also PLD
PC	program counter
PCB	printed circuit board
PGA	programmable gain amplifier

Description Title: PSoC® 3: CY8C36 Family Datasheet Programmable System-on-Chip (PSoC®) *(continued)* Document Number: 001-53413				
Revision	**ECN**	**Submission Date**	**Orig. of Change**	**Description of Change**
*D	2903576	04/01/10	MKEA	Updated Vb pin in PCB Schematic Updated Tstartup parameter in AC Specifications table Added Load regulation and Line regulation parameters to Inductive Boost Regulator DC Specifications table Updated I_{CC} parameter in LCD Direct Drive DC Specs table Updated I_{OUT} parameter in LCD Direct Drive DC Specs table Updated Table 6-2 and Table 6-3 Added bullets on CapSense in page 1; added CapSense column in Section 12 Removed some references to footnote [1] Changed INC_Rn cycles from 3 to 2 (Table 4-1) Added footnote in PLL AC Specification table Added PLL intermediate frequency row with footnote in PLL AC Specs table Added UDBs subsection under 11.6 Digital Peripherals Updated Figure 2-6 (PCB Layout) Updated Pin Descriptions section and modified Figures 6-6, 6-8, 6-9 Updated LVD in Tables 6-2 and 6-3; modified Low-power modes bullet in page 1 Added note to Figures 2-5 and 6-2; Updated Figure 6-2 to add capacitors for V_{DDA} and V_{DDD} pins. Changed V_{REF} from 0.9 to 0.1% Updated boost converter section (6.2.2) Updated Tstartup values in Table 11-3. Removed IPOR rows from Table 11-68. Updated 6.3.1.1, Power Voltage Level Monitors. Updated section 5.2 and Table 11-2 to correct suggestion of execution from flash. Updated V_{REF} specs in Table 11-21. Updated IDAC uncompensated gain error in Table 11-25. Updated Delay from Interrupt signal input to ISR code execution from ISR code in Table11- 72. Removed other line in table. Added sentence to last paragraph of section 6.1.1.3. Updated T_{RESP}, high and low-power modes, in Table 11-24. Updated f_TCK values in Table 11-73 and f_SWDCK values in Table 11-74. Updated SNR condition in Table 11-20. Corrected unit of measurement in Table 11-21. Updated sleep wakeup time in Table 6-3 and Tsleep in Table 11-3. Added 1.71 V <= V_{DDD} < 3.3 V, SWD over USBIO pins value to Table 11-74. Removed mention of hibernate reset (HRES) from page 1 features, Table 6-3, Section 6.2.1.4, Section 6.3, and Section 6.3.1.1. Change PPOR/PRES to TBDs in Section 6.3.1.1, Section 6.4.1.6 (changed PPOR to reset), Table 11-3 (changed PPOR to PRES), Table 11-68 (changed title, values TBD), and Table 11-69 (changed PPOR_TR to PRES_TR). Added sentence saying that LVD circuits can generate a reset to Section 6.3.1.1. Changed I_{DD} values on page 1, page 5, and Table 11-2. Changed resume time value in Section 6.2.1.3. Changed ESD HBM value in Table 11-1. Changed sample rate row in Table 11-20. Removed V_{DDA} = 1.65 V rows and changed BWag value in Table 11-22. Changed V_{IOFF} values and changed CMRR value in Table 11-23. Changed INL max value in Table 11-27. Added max value to the Quiescent current specs in Tables 11-29 and 11-31. Changed occurrences of “Block” to “Row” and deleted the “ECC not included” footnote in Table 11-57. Changed max response time value in Tables 11-69 and 11-71. Changed the Startup time in Table 11-79. Added condition to intermediate frequency row in Table 11-85. Added row to Table 11-69. Added brown out note to Section 11.8.1.

Description Title: PSoC® 3: CY8C36 Family Datasheet Programmable System-on-Chip (PSoC®) *(continued)* Document Number: 001-53413				
Revision	**ECN**	**Submission Date**	**Orig. of Change**	**Description of Change**
*T	4188568	11/14/2013	MKEA	Added SIO Comparator Specifications. Corrected typo in the V_{REF} parameter in the Voltage Reference Specifications. Added CSP information in Packaging and Ordering Information sections. Updated delta-sigma V_{OS} spec conditions.
*U	4385782	05/21/2014	MKEA	Updated General Description and Features. Added More Information and PSoC Creator sections. Updated 100-pin TQFP package diagram.
*V	4708125	03/31/2015	MKEA	Added INL4 and DNL4 specs in VDAC DC Specifications. Updated Figure 6-11. Added second note after Figure 6-4. Added a reference to Fig 6-1 in *Section 6.1.1* and *Section 6.1.2*. Updated *Section 6.2.2*. Added *Section 7.8.1*. Updated Boost specifications.
*W	4807497	06/23/2015	MKEA	Added reference to code examples in More Information. Updated typ value of TWRITE from 2 to 10 in EEPROM AC specs table. Changed “Device supply for USB operation" to "Device supply (VDDD) for USB operation" in USB DC Specifications. Clarified power supply sequencing and margin for VDDA and VDDD. Updated Serial Wire Debug Interface with limitations of debugging on Port 15. Updated Section 11.7.5. Updated Delta-sigma ADC DC Specifications
*X	4932879	09/24/2015	MKEA	Changed the Regulator Output Capacitor min and max from "-" to 0.9 and 1.1, respectively. Added reference to AN54439 in Section 11.9.3. Added MHz ECO DC specs table. Removed references to IPOR rearm issues in Section 6.3.1.1. Table 6-1: Changed DSI Fmax to 33 MHz. Figure 6-1: Changed External I/O or DSI to 0-33 MHz. Table 11-10: Changed Fgpioin Max to 33 MHz. Table 11-12: Changed Fsioin Max to 33 MHz.
*Y	5322536	06/27/2016	MKEA	Updated More Information. Corrected typos in External Electrical Connections. Added links to CAD Libraries in Section 2.